TOSHIBA Photocoupler GaAs Ired & Photo−Transistor

TLP131

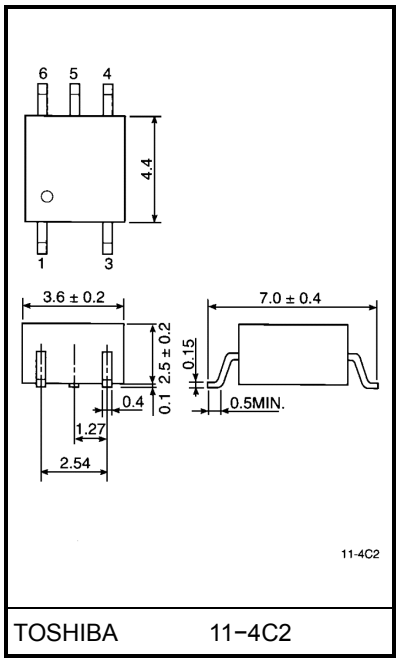
Office Machine
Programmable Controllers
AC / DC−Input Module
Telecommunication

The TOSHIBA mini flat coupler TLP131 is a small outline coupler, suitable for surface mount assembly.
TLP131 consists of a photo transistor, optically coupled to a gallium arsenide infrared emitting diode.

- Collector−emitter voltage: 80V (min.)
- Current transfer ratio: 50% (min.)
  Rank GB: 100% (min.)
- Isolation voltage: 3750Vrms (min.)
- UL recognized: UL1577, file No. E67349

TLP131 base terminal is for the improvement of speed, reduction of dark current, and enable operation.

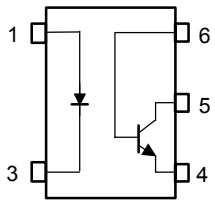
Unit in mm



TOSHIBA 11−4C2

Weight: 0.09 g

Pin Configurations (top view)



1 : Anode
3 : Cathode
4 : Emitter
5 : Collector
6 : Base

Current Transfer Ratio

Type	Classification	Current Transfer Ratio (%) (I_C / I_F) I_F = 5mA, V_{CE} = 5V, Ta = 25°C		Marking Of Classification
		Min.	Max.	
TLP131	(None)	50	600	BLANK, Y, Y■, G, G■, B, B■, GB
	Rank Y	50	150	Y, Y■
	Rank GR	100	300	G, G■
	Rank GB	100	600	G, G■, B, B■, GB

Note: Application type name for certiffication test,please use standard product type name,i.e.
TLP131(GB): TLP131

Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit
LED	Forward current	I_F	50	mA
	Forward current derating (Ta≥53°C)	ΔI_F / °C	−0.7	mA / °C
	Peak forward current (100μs pulse,100pps)	I_{FP}	1	A
	Reverse voltage	V_R	5	V
	Junction temperature	T_j	125	°C
Detector	Collector−emitter voltage	V_{CEO}	80	V
	Collector−base voltage	V_{CBO}	80	V
	Emitter−collector voltage	V_{ECO}	7	V
	Emitter−base voltage	V_{EBO}	7	V
	Collector current	I_C	50	mA
	Peak collector current (10ms pulse,100pps)	I_{CP}	100	mA
	Power dissipation	P_C	150	mW
	Power dissipation derationg (Ta ≥ 25°C)	ΔP_C / °C	−1.5	mW / °C
	Junction temperature	T_j	125	°C
Storage temperature range		T_{stg}	−55~125	°C
Operating temperature range		T_{opr}	−55~100	°C
Lead soldering temperature (10s)		T_{sol}	260	°C
Total package power dissipation		P_T	200	mW
Total package power dissipation derating (Ta ≥ 25°C)		ΔP_T / °C	−2.0	mW / °C
Isolation voltage (AC, 1min., RH≤ 60%) (Note 1)		BV_S	3750	Vrms

(Note 1) Device considered a two terminal device: Pins 1 and 3 shorted together, and pins 4, 5 and 6 shorted together.

Recommended Operating Conditions

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Supply voltage	V_{CC}	—	5	48	V
Forward current	I_F	—	16	25	mA
Collector current	I_C	—	1	10	mA
Operating temperature	T_{opr}	−25	—	85	°C

Individual Electrical Characteristics (Ta = 25°C)

	Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
LED	Forward voltage	V_F	I_F = 10 mA	1.0	1.15	1.3	V
	Reverse current	I_R	V_R = 5 V	—	—	10	μA
	Capacitance	C_T	V = 0, f = 1 MHz	—	30	—	pF
Detector	Collector−emitter breakdown voltage	$V_{(BR)CEO}$	I_C = 0.5mA	80	—	—	V
	Emitter−collector breakdown voltage	$V_{(BR)ECO}$	I_E = 0.1mA	7	—	—	V
	Collector−base breakdown voltage	$V_{(BR)CBO}$	I_C = 0.1mA	80	—	—	V
	Emitter−base breakdown voltage	$V_{(BR)EBO}$	I_E = 0.1mA	7	—	—	V
	collector dark current	I_{CEO}	V_{CE} = 48V	—	10	100	nA
			V_{CE} = 48V,Ta = 85°C	—	2	50	μA
	Collector dark current	I_{CER}	V_{CE} = 48V,Ta = 85°C R_{BE} = 1MΩ	—	0.5	10	μA
	Collector dark current	I_{CBO}	V_{CB} = 10V	—	0.1	—	nA
	DC forward current gain	h_{FE}	V_{CE} = 5V,I_C = 0.5mA	—	400	—	—
	Capacitance (collector to emitter)	C_{CE}	V = 0, f = 1MHz	—	10	—	pF

Coupled Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Current transfer ratio	I_C / I_F	I_F = 5 mA, V_{CE} = 5 V	50	—	600	%
		Rank GB	100	—	600	
Saturated CTR	I_C / $I_{F\ (sat)}$	I_F = 1 mA, V_{CE} = 0.4 V	—	60	—	%
		Rank GB	30	—	—	
Base photo−current	I_{PB}	I_F = 5mA,V_{CB} = 5V	—	10	—	μA
Collector−emitter saturation voltage	$V_{CE\ (sat)}$	I_C = 2.4 mA, I_F = 8 mA	—	—	0.4	V
		I_C = 0.2 mA, I_F = 1 mA	—	0.2	—	
		Rank GB	—	—	0.4	
Off−state collector current	$I_{C\ (off)}$	I_F = 0.7mA, V_{CE} = 48 V	—	1	10	μA

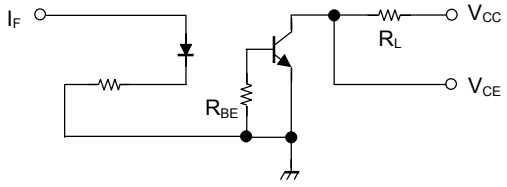
Isolation Characteristics (Ta = 25°C)

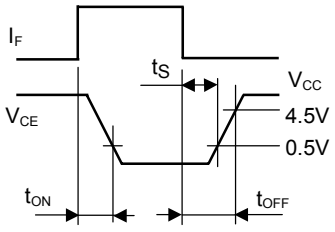
Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Capacitance (input to output)	C_S	V_S = 0, f = 1 MHz	—	0.8	—	pF
Isolation resistance	R_S	V_S = 500 V	5×10^{10}	10^{14}	—	Ω
Isolation voltage	BV_S	AC, 1 minute	3750	—	—	Vrms
		AC, 1 second, in oil	—	10000	—	
		DC, 1 minute, in oil	—	10000	—	Vdc

Switching Characteristics (Ta = 25°C)

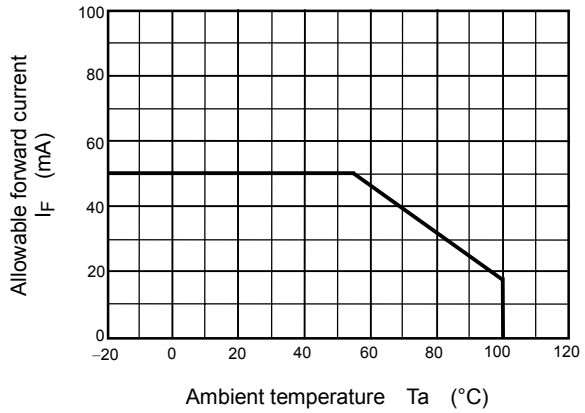
Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Rise time	t_r	V_{CC} = 10 V, I_C = 2 mA R_L = 100Ω	—	2	—	μs
Fall time	t_f		—	3	—	
Turn−on time	t_{on}		—	3	—	
Turn−off time	t_{off}		—	3	—	
Turn−on time	t_{ON}	R_L = 1.9 kΩ%) (Fig.1) R_{BE} = OPEN V_{CC} = 5 V, I_F = 16 mA	—	2	—	μs
Storage time	t_s		—	25	—	
Turn−off time	t_{OFF}		—	40	—	
Turn−on time	t_{ON}	R_L = 1.9 kΩ%) (Fig.1) R_{BE} = 220 kΩ V_{CC} = 5 V, I_F = 16 mA	—	2	—	μs
Storage time	t_s		—	20	—	
Turn−off time	t_{OFF}		—	30	—	

Fig. 1 Switching time test circuit

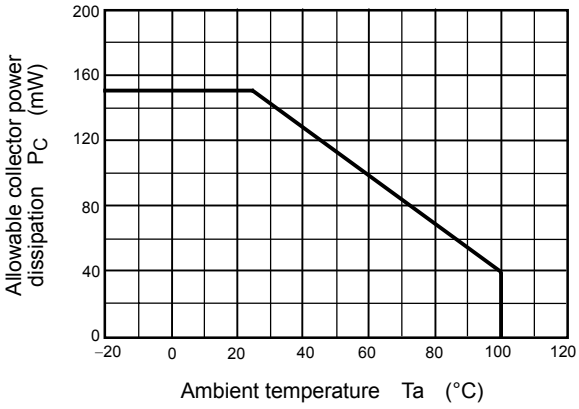




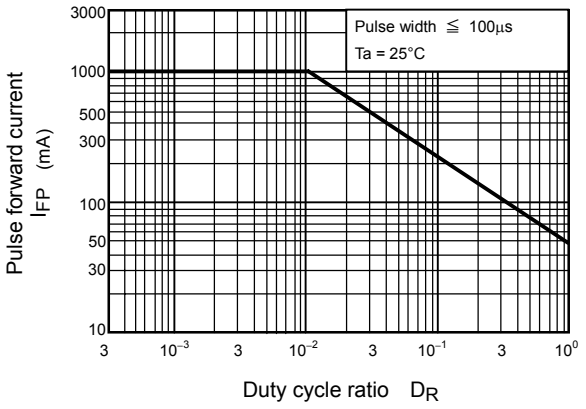
I_F – Ta



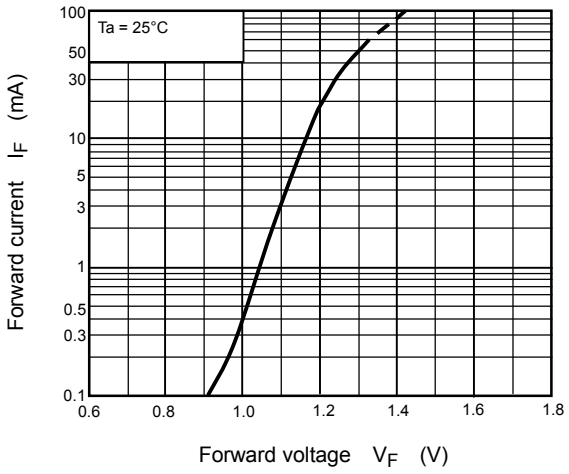
P_C – Ta



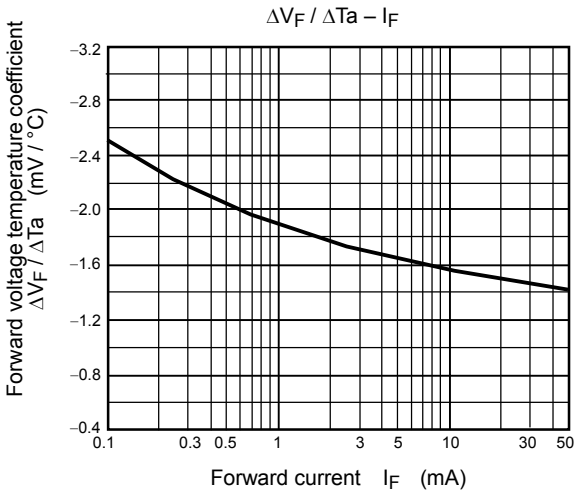
I_{FP} – D_R



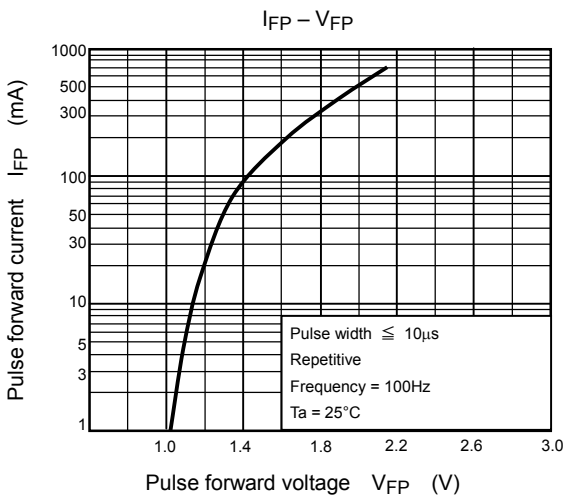
I_F – V_F



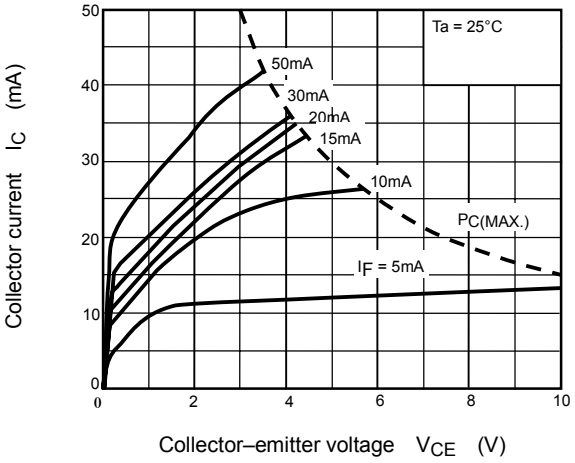
$\Delta V_F / \Delta Ta$ – I_F



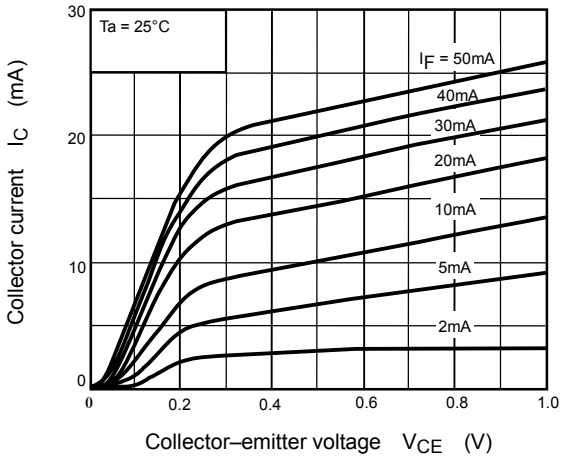
I_{FP} – V_{FP}



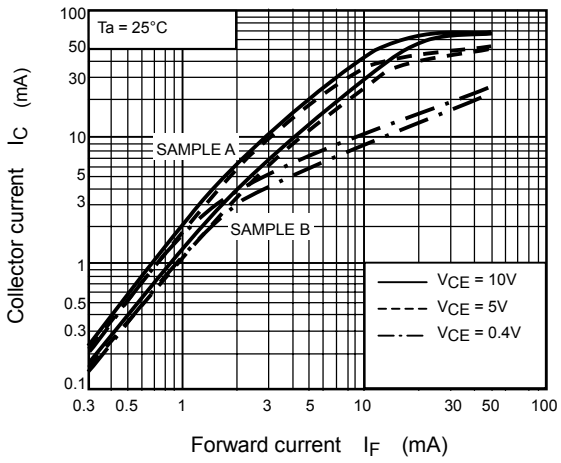
$I_C - V_{CE}$



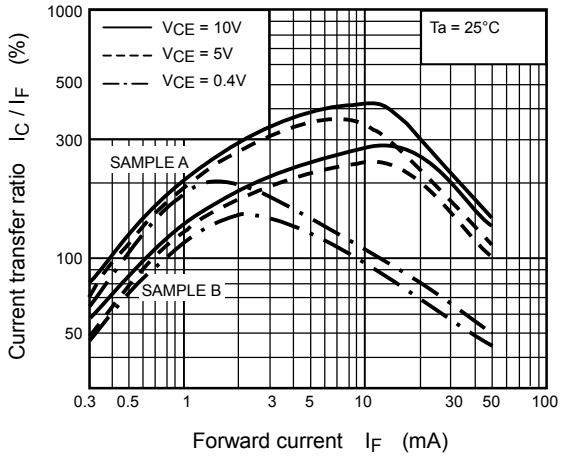
$I_C - V_{CE}$



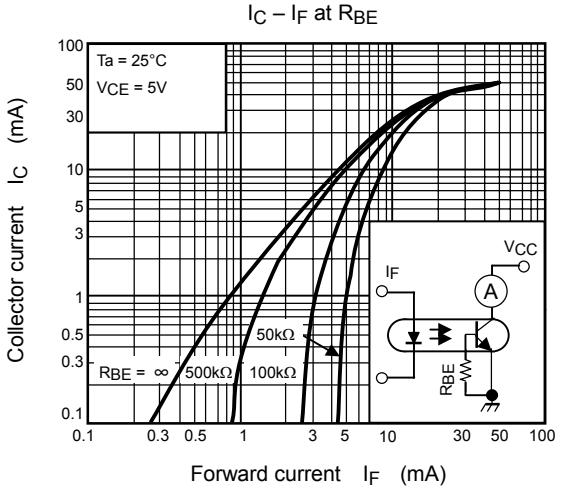
$I_C - I_F$



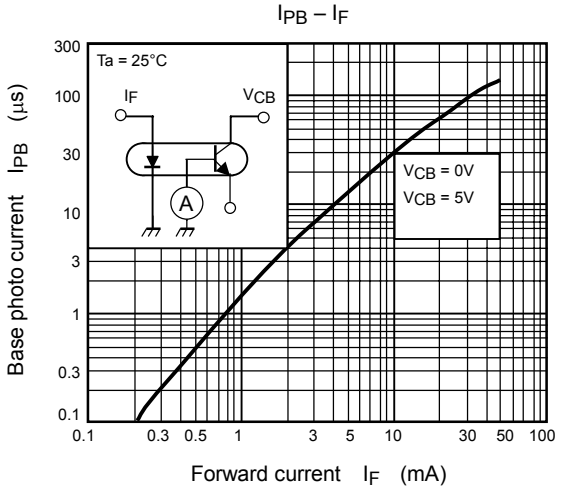
$I_C / I_F - I_F$



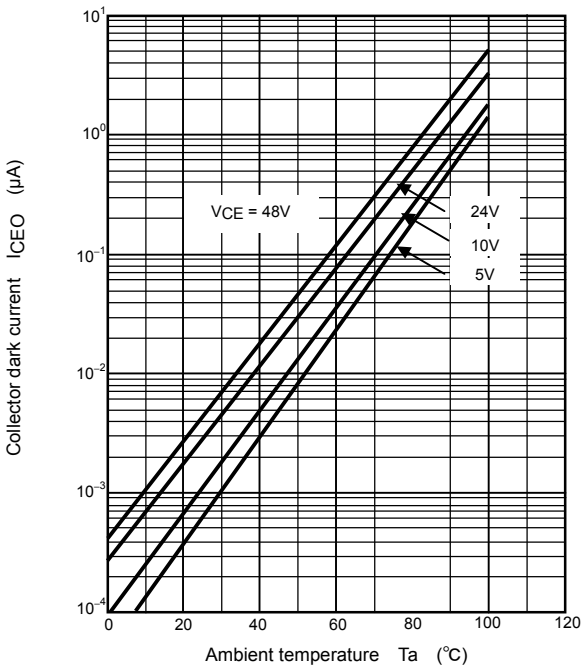
$I_C - I_F$ at R_{BE}



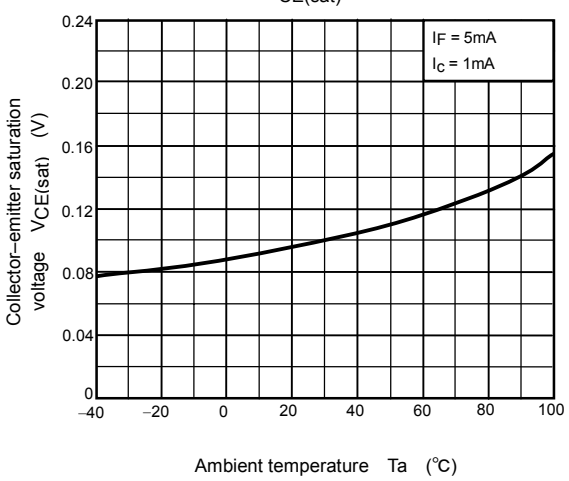
$I_{PB} - I_F$



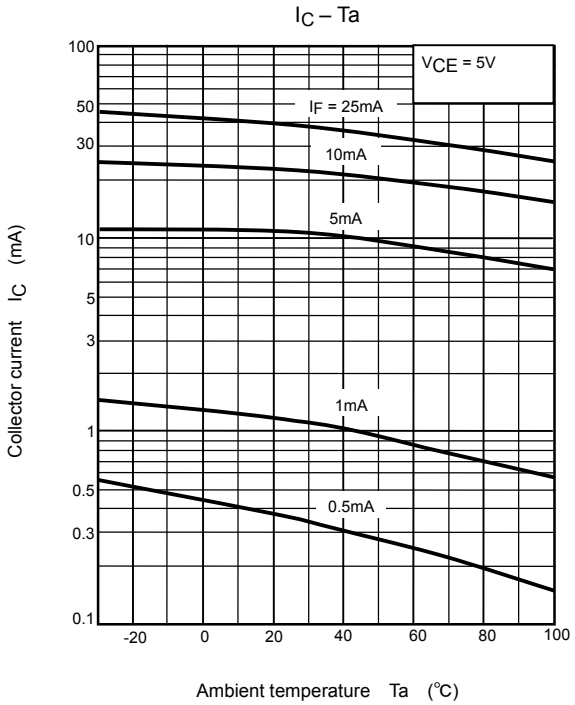
I_{CEO} – Ta



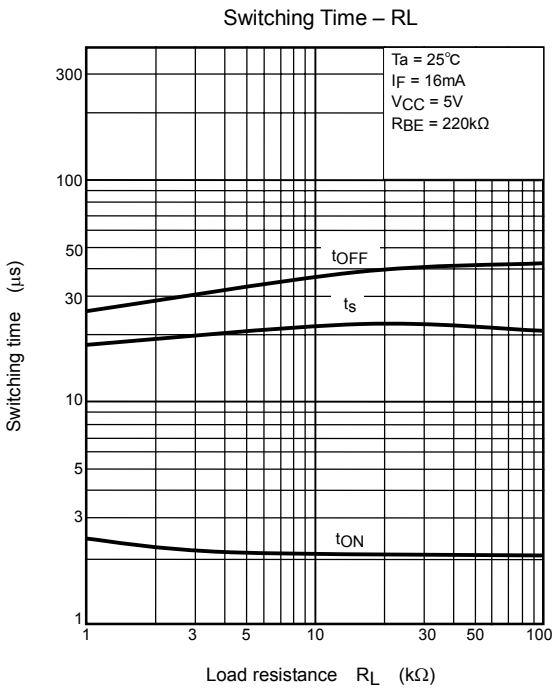
$V_{CE(sat)}$ – Ta



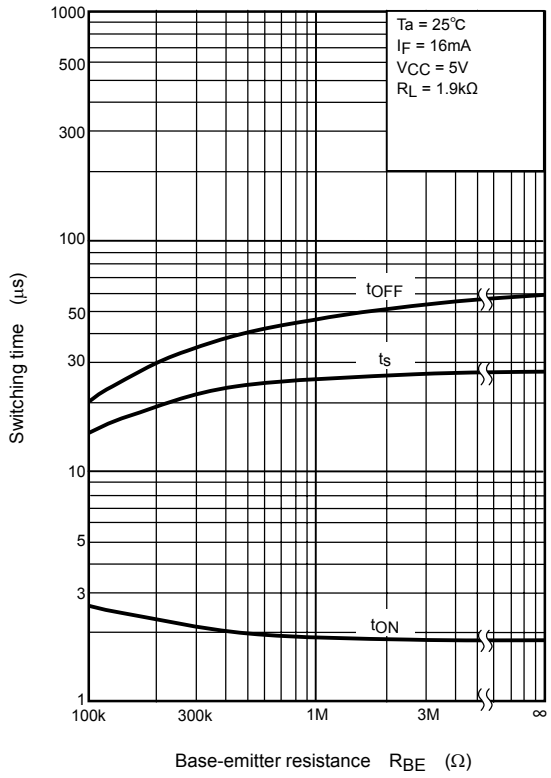
I_C – Ta



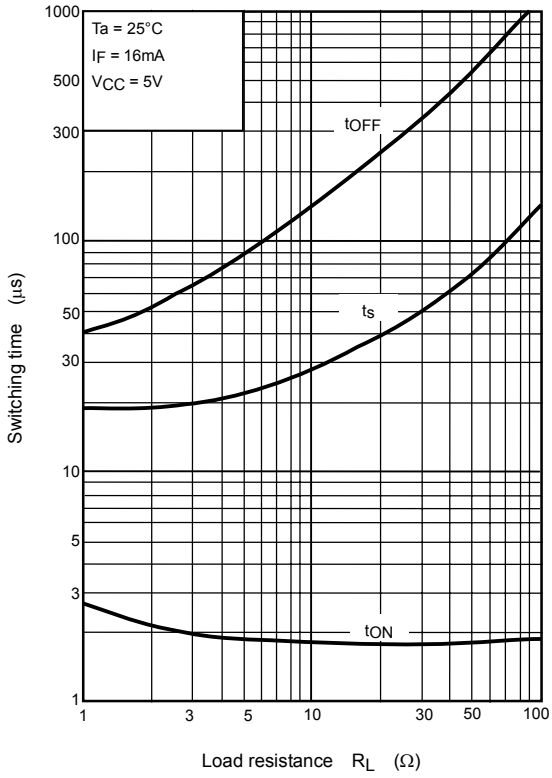
Switching Time – RL



Switching Time – R_{BE}



Switching Time – R_L



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